

晁元國際半導體股份有限公司
MaxPower SiC Semiconductor Co., Ltd.

Change History:

Date	Version	Change Item	Author
2023/7/28	V1.0	First release.	John Ruan

M1P-1200-200E

All Silicon Carbide Power Module

1200V/200A 62mm SiC MOSFET Power Module

Features

- Low $R_{DS(on)}$
- Low surge, low switching loss
- High-speed switching possible
- Halogen Free, RoHS Compliant

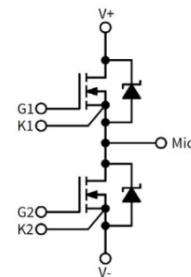
Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Applications

- Motor drive
- Electrified vehicle traction inverter
- Photovoltaics, wind power generation
- Induction heating equipment

Equivalent Circuit Schematic



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V		
V_{GSmax}	Gate - Source Voltage	-8/+25	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	-5/+20	V	Recommended operational values	
I_D	Continuous Drain Current	200 160	A	$V_{GS}=20\text{V}$, $T_{VJ} = 25^\circ\text{C}$ $V_{GS}=20\text{V}$, $T_{VJ} = 150^\circ\text{C}$	
$I_{D,peak}$	Repetitive peak drain current	600	A	Pulsed Drain Current, t_p limited by T_{jmax}	
T_{VJ} , T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		
V_{ISO}	Isolation Test Voltage	4200		AC, 50Hz, 1 min.	

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Electrical Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1200			V	$V_{GS}=0V, I_D=100\mu A$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.50	4.0	V	$V_{GS}=V_{DS}, I_{DS}=100mA, T_{VJ}=25^\circ C$	
			1.80			$V_{GS}=V_{DS}, I_{DS}=100mA, T_{VJ}=150^\circ C$	
I_{DSS}	Zero Gate Voltage Drain Current		32	240	μA	$V_{DS}=1200V, V_{GS}=0V$	
I_{GSS}	Gate-Source Leakage Current		80	360	nA	$V_{GS}=20V, V_{DS}=0V$	
$R_{DS(on)}$	Drain-Source on-state Resistance		4.75	5.25	m Ω	$V_{GS}=20V, I_D=200A, T_{VJ}=25^\circ C$	
			6.42		m Ω	$V_{GS}=20V, I_D=200A, T_{VJ}=150^\circ C$	
C_{iss}	Input Capacitance		19.4		nF	$V_{GS}=0V, V_{DS}=800V, f=1MHz, V_{AC}=25mV$	
C_{oss}	Output Capacitance		118				
C_{rss}	Reverse Transfer Capacitance		0.95				
E_{ON}	Turn-On Switching Energy		14.8		mJ	$V_{DS}=800V, V_{GS}=-5/20V, I_D=200A, R_{G(ext)}=5\Omega, L=80\mu H, di/dt=4kA/\mu s$	
E_{OFF}	Turn-Off Switching Energy		13.5				
$t_{d(on)}$	Turn-On Delay Time		61		ns	$V_{DS}=800V, V_{GS}=-5/20V, I_D=200A, R_{G(ext)}=5\Omega,$	
t_r	Rise Time		57				
$t_{d(off)}$	Turn-Off Delay Time		205				
t_f	Fall Time		46				
Q_{gs}	Gate to Source Charge		228		nC	$V_{DS}=800V, V_{GS}=-5/20V, I_D=200A$	
Q_{gd}	Gate to Drain Charge		315				
Q_g	Total Gate Charge		950				

Reverse Diode Characteristics

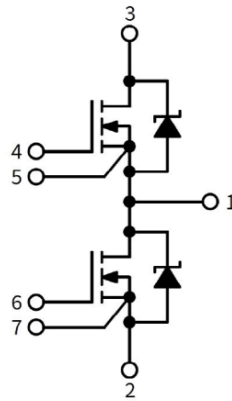
Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.7		V	$V_{GS}=-5V, I_{SD}=160A, T_{VJ}=25^\circ C$	
		3.4		V	$V_{GS}=-5V, I_{SD}=160A, T_{VJ}=150^\circ C$	
I_S	Continuous Diode Forward Current		200	A	$V_{GS}=-5V, T_{VJ}=25^\circ C$	
			180	A	$V_{GS}=-5V, T_{VJ}=150^\circ C$	
I_{rrm}	Peak reverse recovery current		200	A	$V_{GS}=-5V, I_{SD}=160A, V_{R,DS}=800V, T_{VJ}=25^\circ C$	
			340	A	$V_{GS}=-5V, I_{SD}=160A, V_{R,DS}=800V, T_{VJ}=150^\circ C$	
Q_{rr}	Reverse recovery charge		13.8	nC	$V_{GS}=-5V, I_{SD}=160A, V_{R,DS}=800V, T_{VJ}=25^\circ C$	
			26.1	nC	$V_{GS}=-5V, I_{SD}=160A, V_{R,DS}=800V, T_{VJ}=150^\circ C$	

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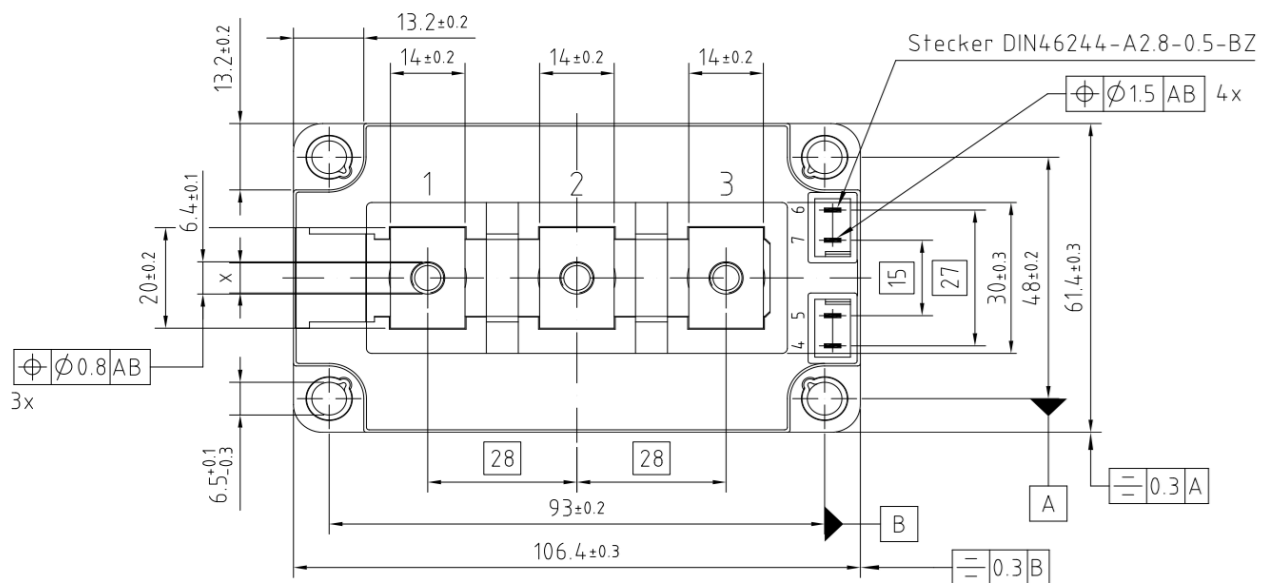
Package Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$L_{s,DS}$	Stray inductance of module		10.5		nH	$T_c = 25^\circ\text{C}$	
M_C	Mounting torque for module mounting	4.0	5.0	6.0	Nm	Screw M6 baseplate to heatsink	
M_T	Mounting torque for module power terminal	3.0	4.0	5.0	Nm	Screw M6 power terminal to bus bar	
W_p	Weight		320		g		

Circuit Schematic



Package Dimension



x: M5/M6 depending on type
x: M5/M6 je nach Typ